

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,984,547 B2
APPLICATION NO. : 10/662074
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INVENTOR(S) : Chun Chen, Andrei Mihnea and Kirk Prall

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 4, line 64, after "not", insert --containing--.

Column 5, line 6, before "the target memory cell", insert --of--.

Column 6, line 30, after "rows", insert --not--.

Column 6, line 39, "preformed" should be changed to --performed--.

Column 11, line 48, after "the second potential has a", insert the following text:
--second polarity; applying the second potential to a first well containing the first and--.

Signed and Sealed this

Twentieth Day of November, 2007

A handwritten signature in black ink, reading "Jon W. Dudas", is placed over a rectangular area with a grey, textured background.

JON W. DUDAS
Director of the United States Patent and Trademark Office